## IVPS100-PTB - Improved Vertical Parallel Structure

Tip width characterizer with an array of 5 lines, line width varying from 50 nm to 130 nm in steps of 20 nm.

Designed in collaboration with Physikalisch Technische Bundesanstalt, Braunschweig, Germany.

## **Specifications**

Material Silicon

increasing from 50 nm to 130 nm in steps of 20

Width of line nm

actual linewidth is delivered for each chip

Pitch  $500 \text{ nm} \pm 10 \text{nm}$ 

Depth of line  $\sim 1 \mu m$ 

Surface/sidewall angle < 90° ± 0,5°

Sidewall parallelity < 1°

Top corner radius < 10 nm

Probe tip characterizers are used to check the shape and the dimension of the probe tip.

Each cell is numbered, which facilitates recalibration at the identical position.

## Layout:

4 quadrands with 25 cells each, on 6 x 6 mm silicon chip

